

General Description

The AGM60P35F combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

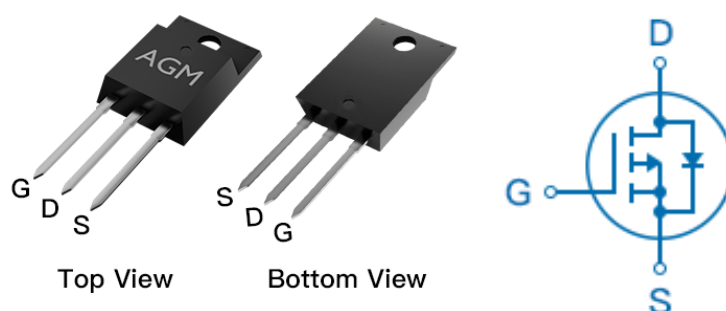
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDS(ON)	ID
-60	17mΩ	-52A

TO-220F Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM60P35F	AGM60P35F	TO-220F	----	----	1000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-60	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	-52	A
	Drain Current-Continuous(Tc=100°C)	-24	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	-208	A
PD	Maximum Power Dissipation(Tc=25°C)	50	w
	Maximum Power Dissipation(Tc=100°C)	20	w
EAS	Avalanche energy (Note 3)	324	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	65	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	2.5	°C/W

Table 3. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-60V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	-1.6	-2.2	V
gFS	Forward Transconductance	VDS=-5V,ID=-6A	--	27	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-15A	--	17	22	mΩ
		VGS=-4.5V, ID=-6A	--	19	25	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-30V,VGS=0V, F=1MHZ	--	4550	--	pF
Coss	Output Capacitance		--	225	--	pF
Crss	Reverse Transfer Capacitance		--	198	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	10.3	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-30V, ID=-1A,RL=15Ω RGEN=2.5Ω	--	66	--	nS
tr	Turn-on Rise Time		--	99	--	nS
td(off)	Turn-Off Delay Time		--	38	--	nS
tf	Turn-Off Fall Time		--	10	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-15V, ID=-12A	--	70	--	nC
Qgs	Gate-Source Charge		--	19	--	nC
Qgd	Gate-Drain Charge		--	10	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-52	A
VSD	Forward on Voltage	VGS=0V,IS=-15A	--	--	-1.2	V
trr	Reverse Recovery Time	Isd=-15A ,	--	--	--	ns
Qrr	Reverse Recovery Charge	dI/dt=100A/μs , TJ=25℃	--	--	--	nc

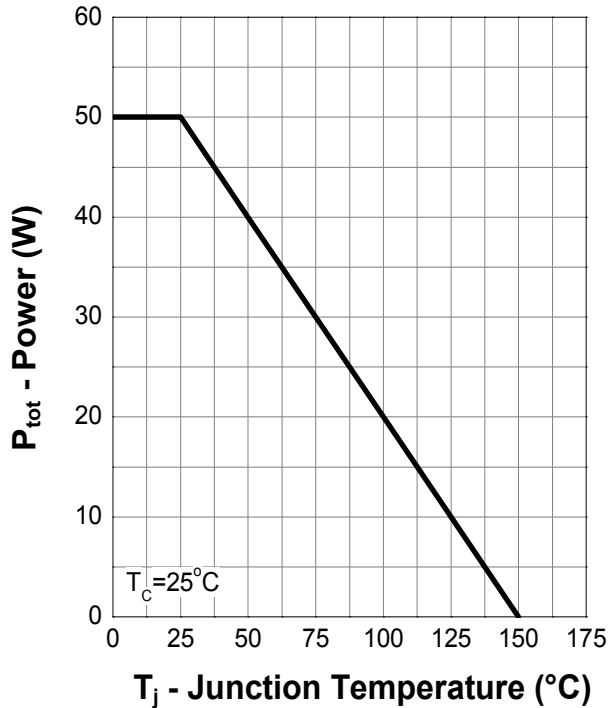
Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

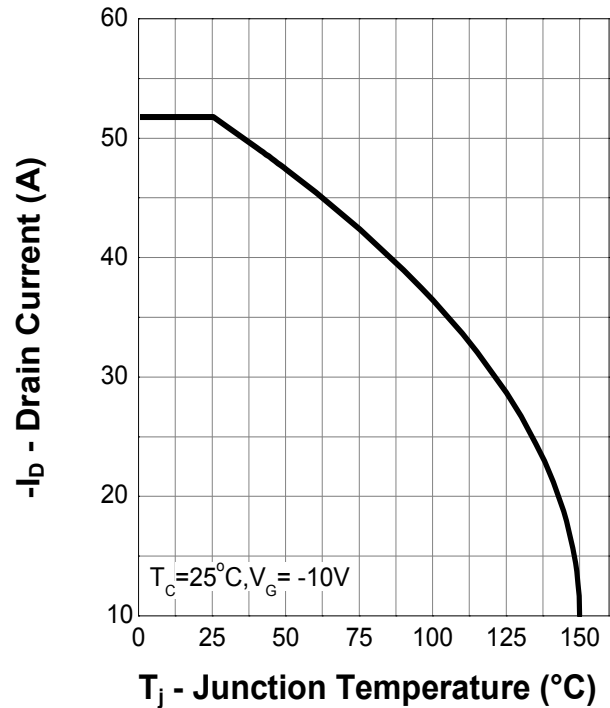
Notes 3.EAS condition: T_J=25°C, V_{DD}=-30V, V_{gs}=-10V, ID=-36A, L=0.5mH, R_G=25ohm

Typical Characteristics (Cont.)

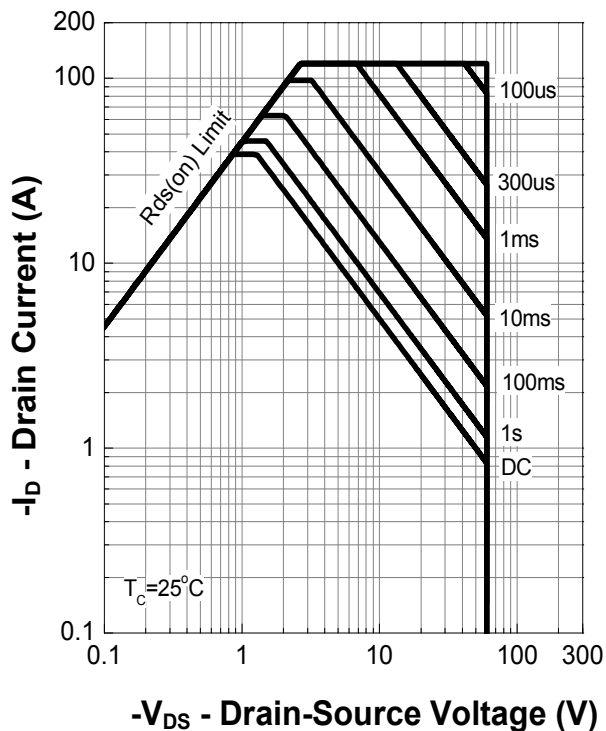
Power Capability



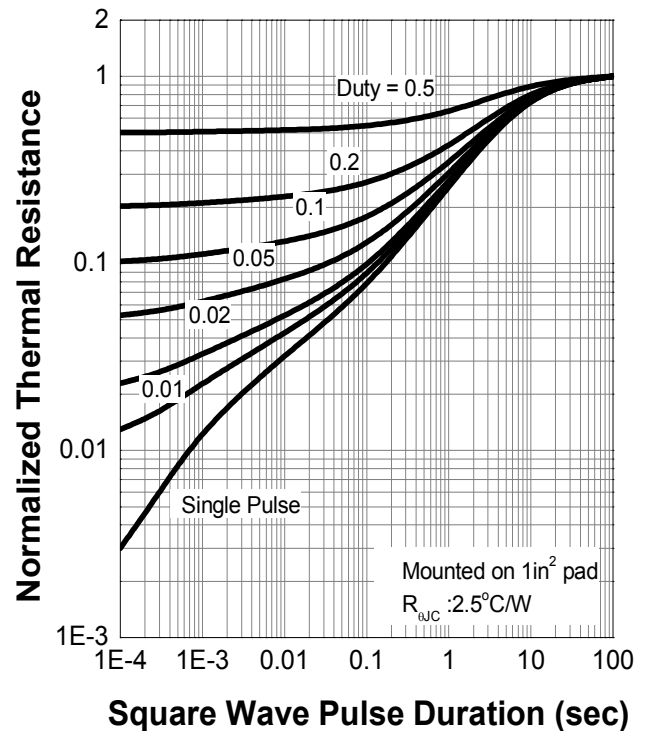
Current Capability



Safe Operation Area

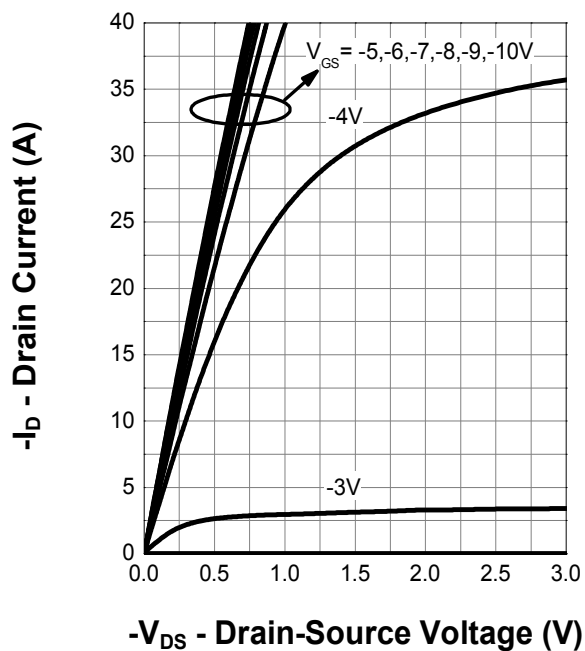


Transient Thermal Impedance

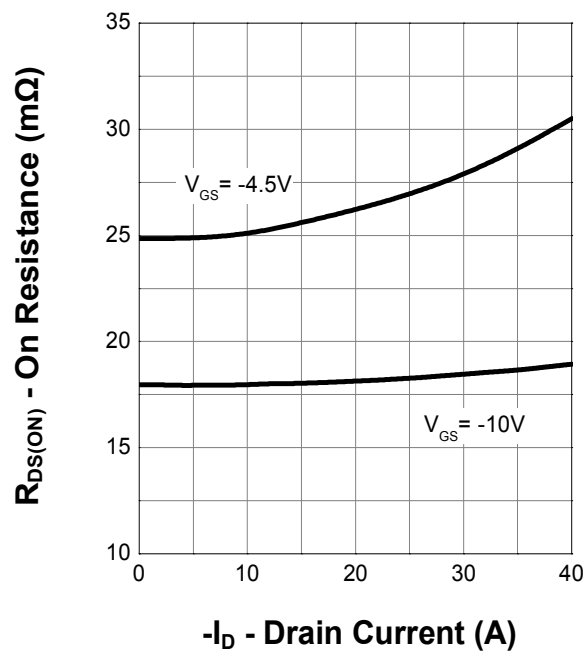


Typical Characteristics (Cont.)

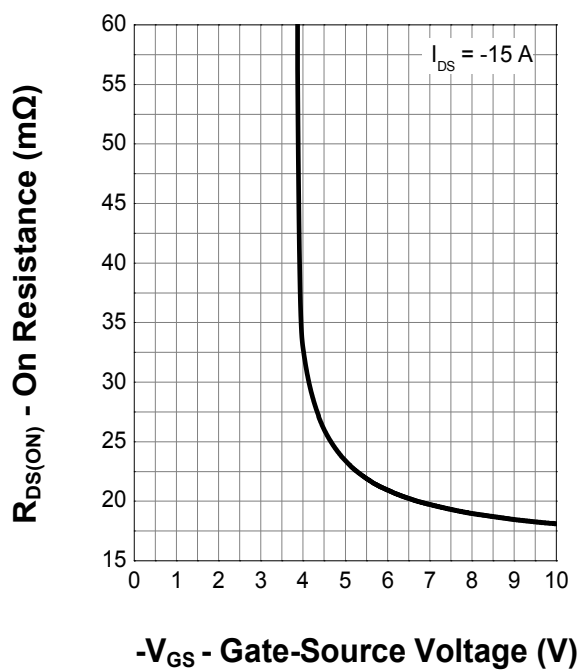
Output Characteristics



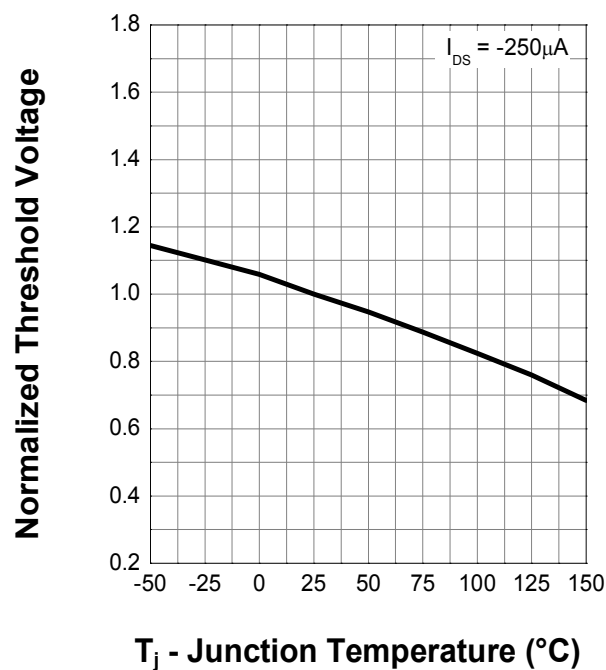
Drain-Source On Resistance



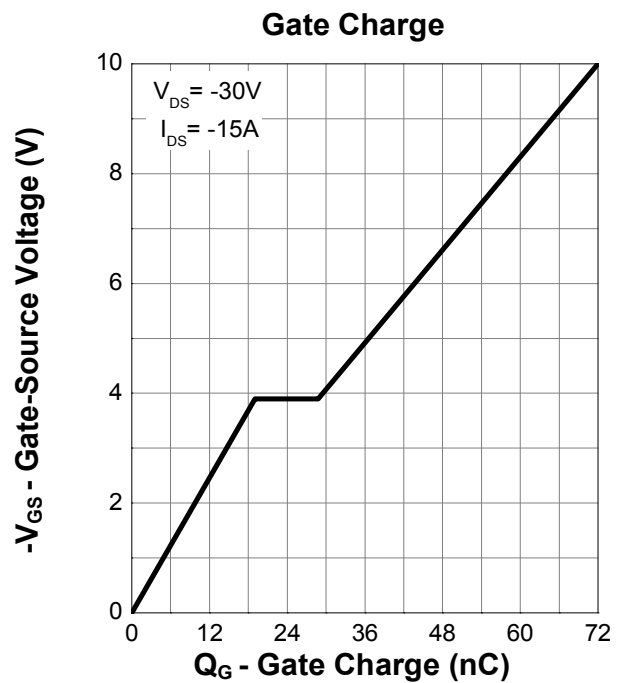
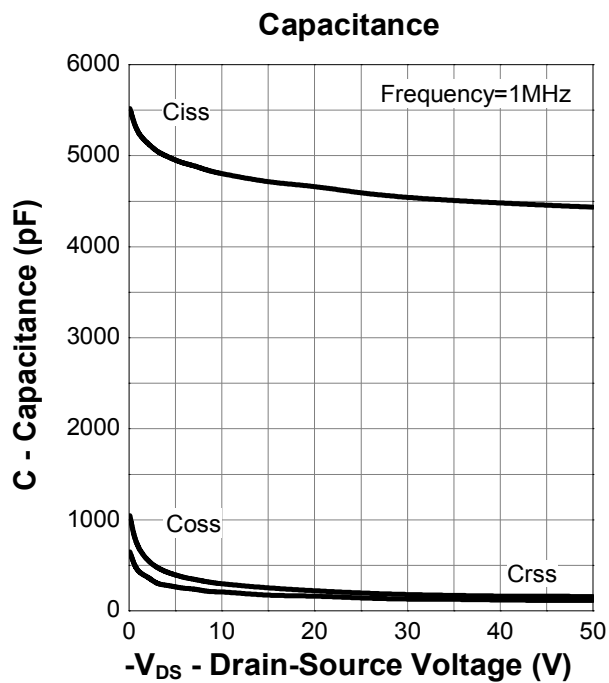
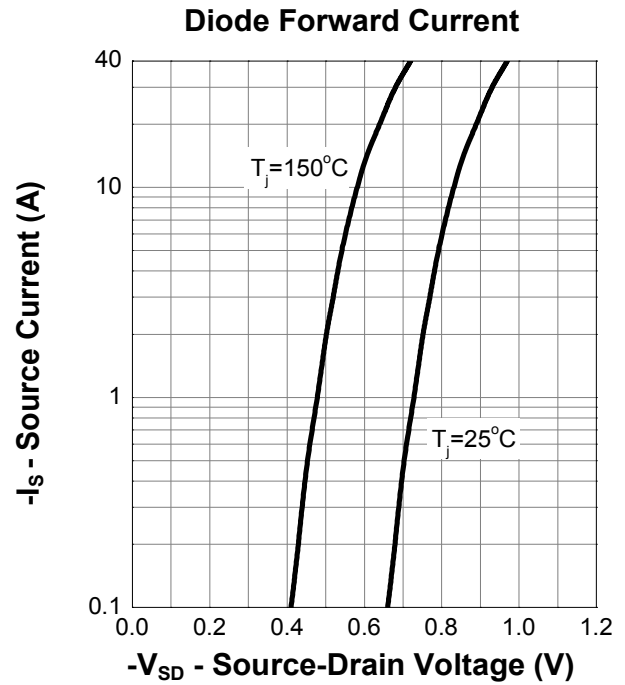
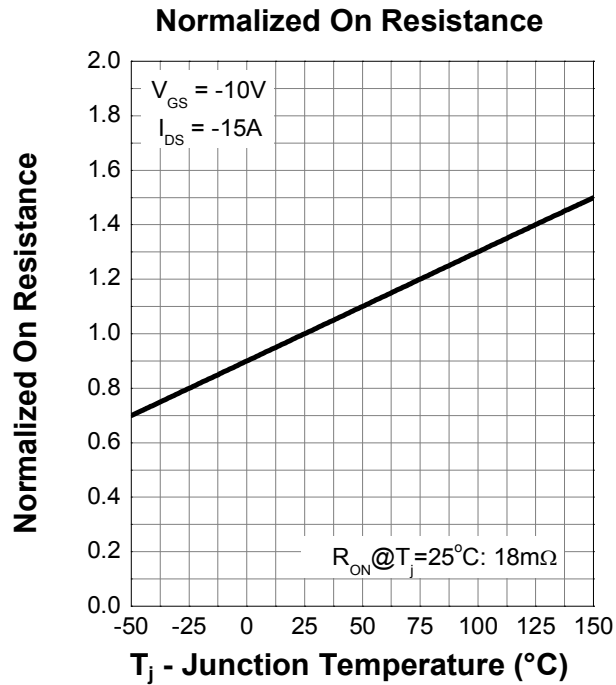
Transfer Characteristics



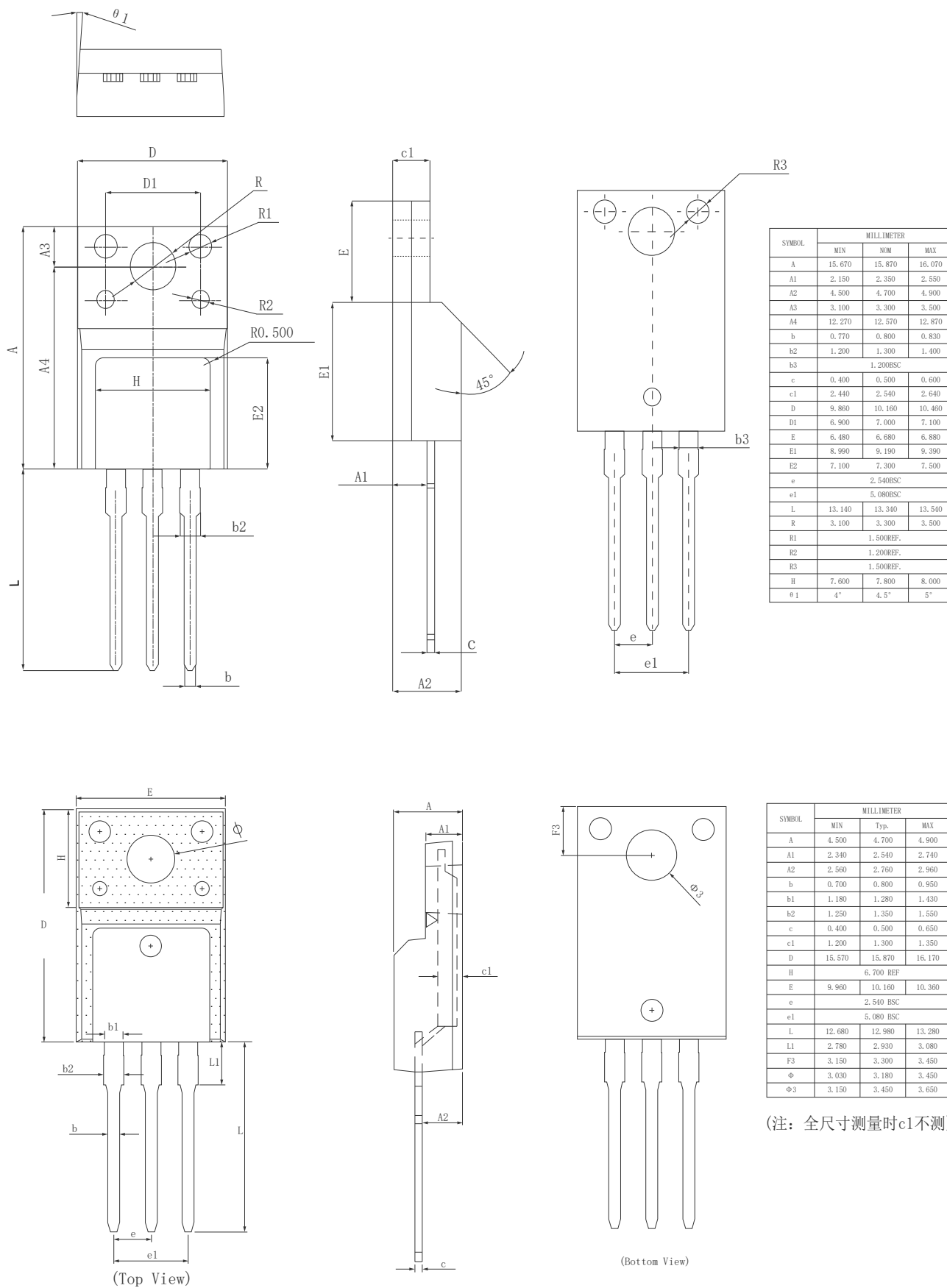
Normalized Threshold Voltage



Typical Characteristics (Cont.)

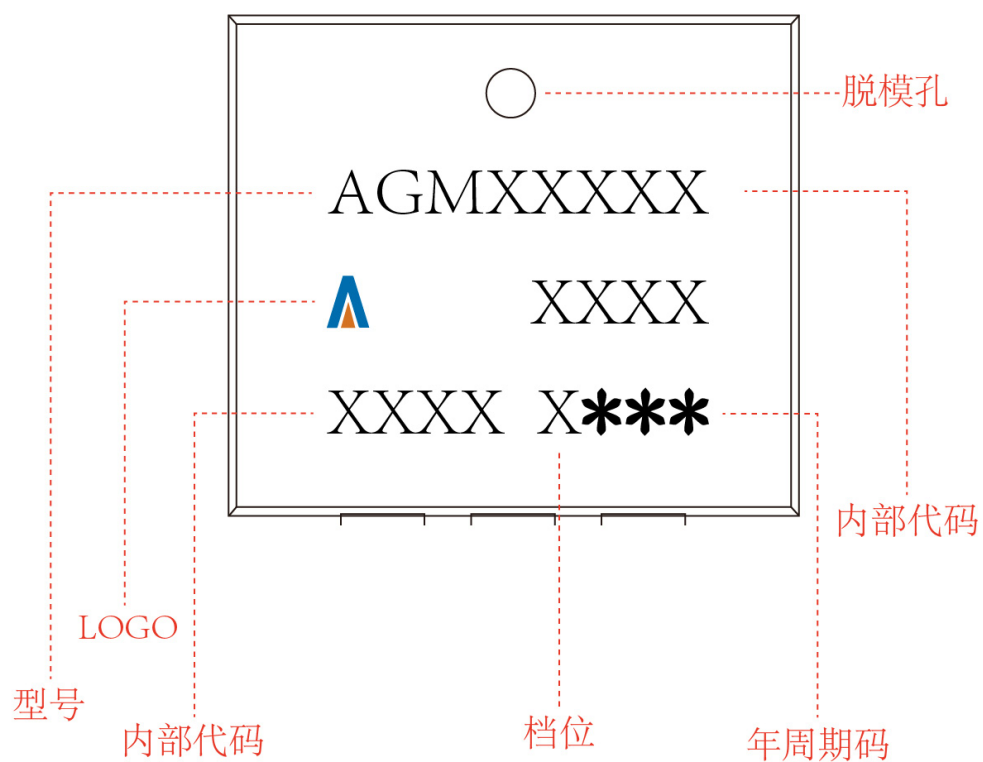


Dimensions (TO-220F)



TO-220F

Marking Instructions:



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